Atty. reference: Al 425NP

CLAIM AMENDMENTS:

1. (Currently Amended) A wiring board to which a semiconductor chip is to be bonded while directing a surface of the semiconductor chip toward the wiring board, the wiring board comprising:

a connection electrode formed on a bonding surface to which the semiconductor chip is to be bonded, the connection electrode being for a connection with the semiconductor chip;

an insulating film formed on the bonding surface, the insulating film having an opening to expose the connection electrode; and

a low-melting-point metallic part provided on the connection electrode in the opening, the low-melting-point metallic part being made of a low-melting-point metallic material whose solidus temperature is lower than that of the connection electrode, wherein a volume of an inside of the opening is greater than a sum of a volume of the connection electrode and a volume of the low-melting-point metallic part.

- 2. (Canceled)
- 3. (Currently Amended) A semiconductor device comprising:
- a wiring board; and

a semiconductor chip having a projection electrode formed on a surface on which a functional element is formed, the projection electrode being electrically connected to the functional element, the semiconductor chip being bonded to a

Atty. reference: AI 425NP

bonding surface of the wiring board with the surface of the semiconductor chip facing the bonding surface;

the wiring board including:

a connection electrode formed on the bonding surface, the connection electrode being used to make a connection with the semiconductor chip;

an insulating film formed on the bonding surface, the insulating film having an opening to expose the connection electrode; and

a low-melting-point metallic part provided on the connection electrode in the opening, the low-melting-point metallic part being made of a low-melting-point metallic material whose solidus temperature is lower than that of the connection electrode, wherein a volume of an inside of the opening is greater than a sum of a volume of the connection electrode and a volume of the low-melting-point metallic part.